



Gr. 2818

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**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

Applicant: Leonard Forbes et al.  
Title: DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE INSULATOR  
Docket No.: 303.354US2 Serial No.: 09/135,413  
Filed: August 14, 1998 Due Date: May 23, 1999  
Examiner: Viet Q. Nguyen Group Art Unit: 2818

Assistant Commissioner for Patents  
Washington, D.C. 20231

We are transmitting herewith the following attached items (as indicated with an "X"):

- X A return postcard.
- X An Amendment and Response (8 Pages).
- X A check in the amount of \$192.00 to cover the fee for additional claims as calculated below.
- X Communication Concerning Copending Applications (2 pgs.).

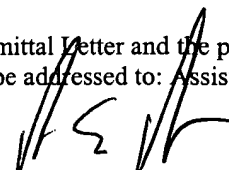
If an additional fee is required due to changes to the claims, the fee has been calculated as follows:

CLAIMS AS AMENDED						
	(1) Claims Remaining After Amendment		(2) Highest Number Previously Paid For	(3) Present Extra	Rate	Fee
TOTAL CLAIMS	22	-	20	2	x 18 =	\$36.00
INDEPENDENT CLAIMS	5	-	3	2	x 78 =	\$156.00
[ ] MULTIPLE DEPENDENT CLAIMS PRESENTED						\$0.00
TOTAL						\$192.00

Please consider this a PETITION FOR EXTENSION OF TIME for sufficient number of months to enter these papers and please charge any additional required fees or credit overpayment to Deposit Account No. 19-0743.

CERTIFICATE UNDER 37 CFR 1.8: The undersigned hereby certifies that this Transmittal letter and the paper, as described above, are being deposited in the United States Postal Service, as first class mail, in an envelope addressed to: Assistant Commissioner for Patents, Washington, D.C. 20231, on this 14<sup>th</sup> day of May, 1999.

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S/N 09/135,413

PATENT

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Serial No.: 09/135,413

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Docket: 303.354US2

Title: DEAPROM HAVING AMORPHOUS SILICON CARBIDE GATE  
INSULATOR

**AMENDMENT AND RESPONSE**

Assistant Commissioner for Patents  
Washington, D.C. 20231

In response to the Office Action mailed February 23, 1999, please amend the above identified patent application as follows:

**IN THE TITLE**

Please delete the title and replace it with the following: --Method For Operating A DEAPROM Having An Amorphous Silicon Carbide Gate Insulator--.

**IN THE SPECIFICATION**

Please amend the specification by deleting lines 5-18 on page 1 of the originally filed application, beginning with the heading "**Cross Reference To Related Applications.**"

On page 19, lines 26-27, please replace "serial number \_\_\_\_" with --serial number 08/903,453--.

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**IN THE CLAIMS**

Please cancel claims 25-27 and 39-42.

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Please amend the claims as follows:

19. (Amended) A method of using a floating gate transistor having a floating gate electrode and an adjacent amorphous silicon carbide (a-SiC) gate insulator between the floating gate electrode and a substrate, the method comprising:

storing data by changing [the] a charge of the floating gate electrode;

reading data by detecting a current between a source and a drain in the substrate; and

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01 FC:102  
02 FC:103